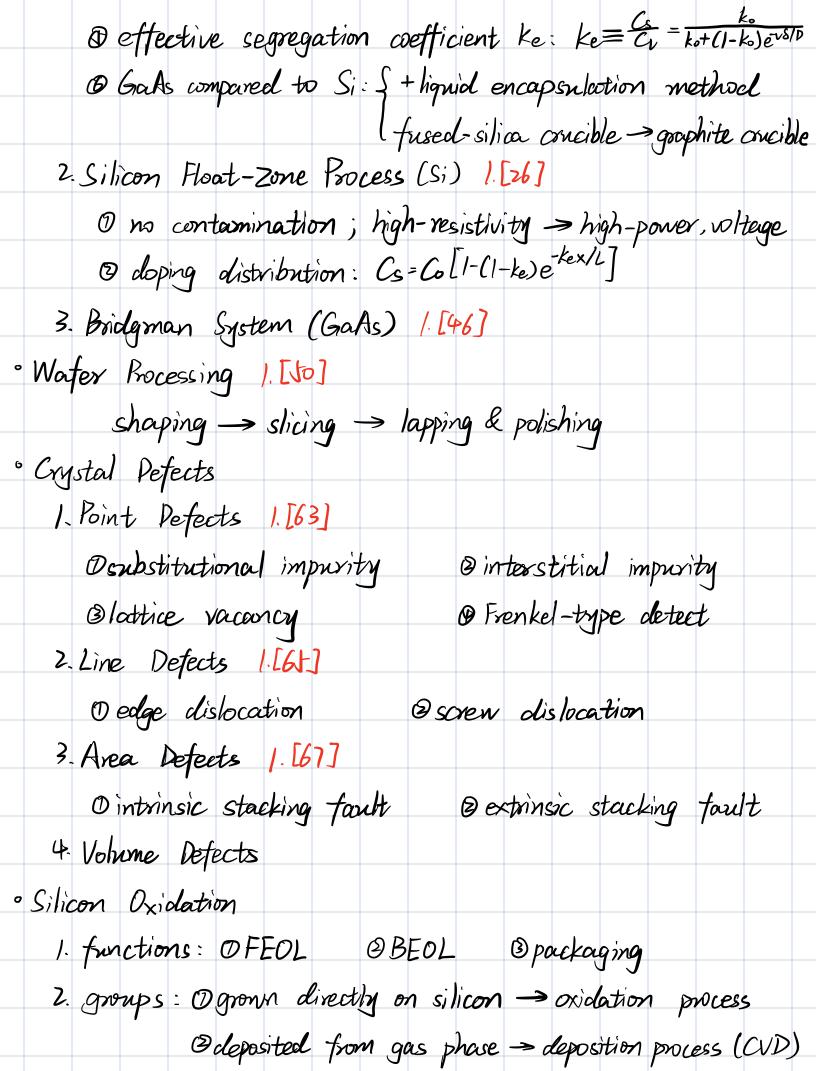
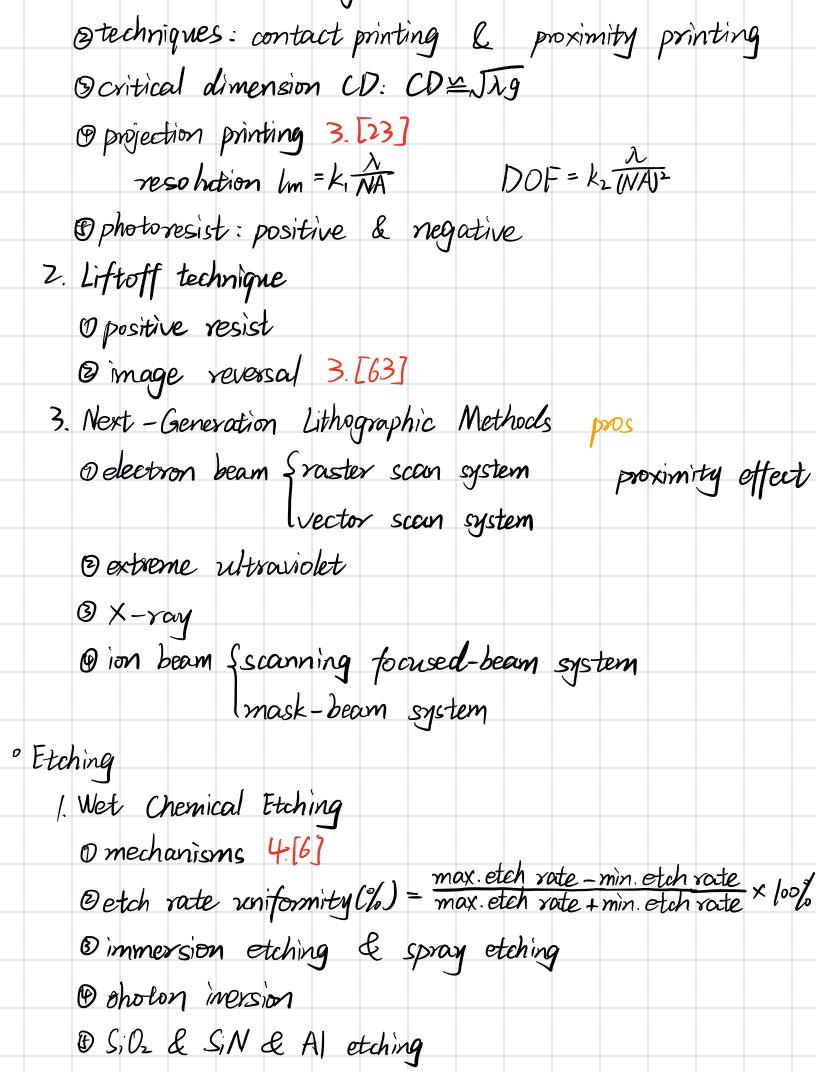
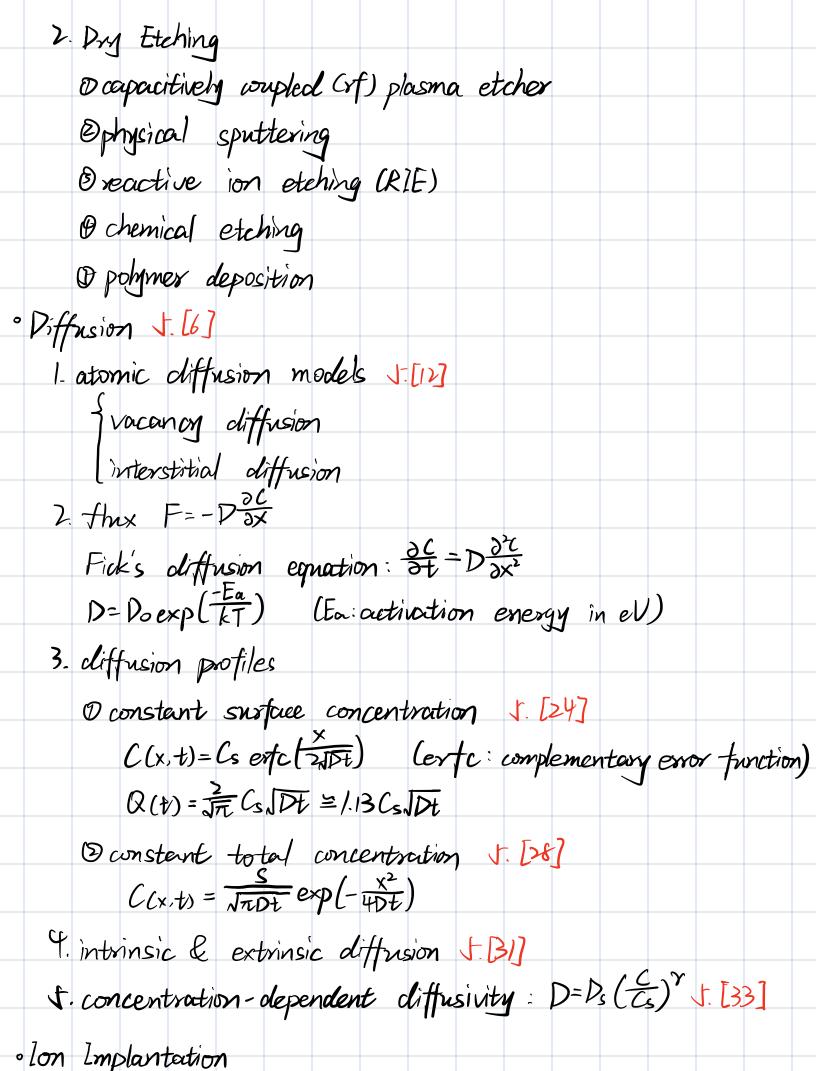
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	1.	the	*	F, =	$D\frac{d}{dt}$	<u>C</u> ≃	DLC	5-(5) ×)	F_=	KCs						
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1. medium-current ion implantor 6.[7]	
2 ion distribution: Gaussian	
3. ion stopping SO transfer its energy to the target muclei	
	ud
The of electrons around the target's atoms	
$\frac{dE}{dx} = S_n(E) + S_e(E)$	
4 ion channeling -> the exponential tail	
minimized techniques { O blocking amosphous layer	
Omisorientation of the waters	
3 pre-damage the water	
5 implant damage 6. [49] heavy & light ions	
6 annealing	
* Epitaxial Growth Schemical vagor deposition (CVD)	
(molecular beam epitaxy (MBE)	
1. CVD 7.[7]	
Ovapor-phase epitaxy (VPE)	
0 { at atmospheric pressure (APCVD)	
(at low pressure (LPCVD)	
Chorizontal Chorizontal	
1) Srisceptors [horizontal] 7. [1]	
(barrel	
2. MBE 7.[18]	
O molecular impingement rate $S = P(2\pi m kT)^{-\frac{1}{2}}$	
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